
2SK2685

GaAs HEMT

HITACHI

ADE-208-400

1st. Edition

Application

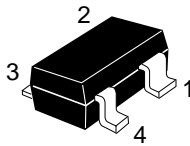
UHF low noise amplifier

Features

- Excellent low noise characteristics.
 $F_{min} = 0.83 \text{ dB Typ. (3 V, 10 mA, 2 GHz)}$
- High associated gain.
 $G_a = 17 \text{ dB Typ. (3 V, 10 mA, 2 GHz)}$
- High voltage.
 $V_{DS} = 6 \text{ or more voltage.}$
- Small package. (CMPAK-4)

Outline

CMPAK-4



1. Source
2. Gate
3. Source
4. Drain

Absolute Maximum Ratings (Ta = 25°C)

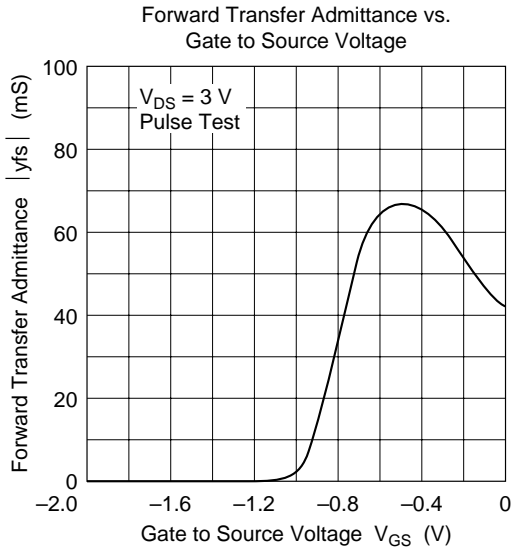
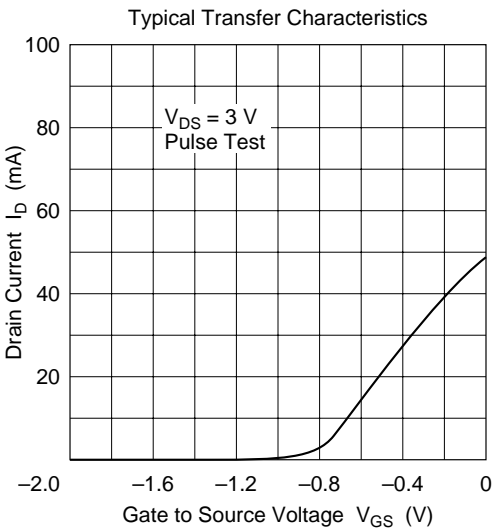
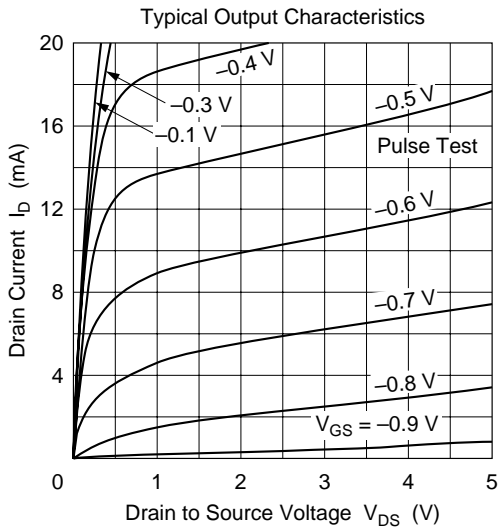
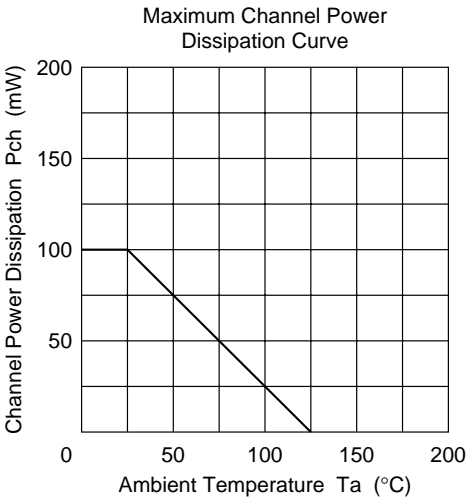
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	6	V
Gate to source voltage	V_{GSO}	−6	V
Gate to drain voltage	V_{GDO}	−7	V
Drain current	I_D	20	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	125	°C
Storage temperature	Tstg	−55 to +125	°C

Attention: This device is very sensitive to electro static discharge.
It is recommended to adopt appropriate cautions when handling this transistor.

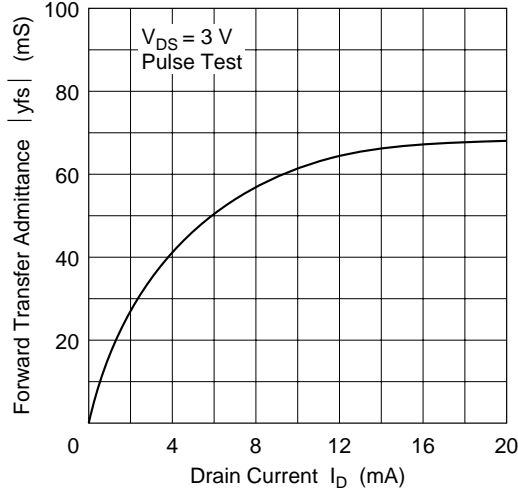
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to source leak current	I_{GSS}	—	—	−20	μA	$V_{GS} = -6\text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	−0.3	—	−2.0	V	$V_{DS} = 3\text{ V}, I_D = 100\text{ }\mu\text{A}$
Drain current	I_{DSS}	35	50	70	mA	$V_{DS} = 3\text{ V}, V_{GS} = 0$ (Pulse Test)
Forward transfer admittance	$ y_{fs} $	40	60	—	mS	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA},$ $f = 1\text{ kHz}$
Associated gain	Ga	—	17.0	—	dB	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA},$ $f = 2\text{ GHz}$
Associated gain	Ga	—	15.2	—	dB	$V_{DS} = 3\text{ V}, I_D = 3\text{ mA},$ $f = 2\text{ GHz}$
Associated gain	Ga	16	21.4	—	dB	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA},$ $f = 900\text{ MHz}$
Associated gain	Ga	—	19.7	—	dB	$V_{DS} = 3\text{ V}, I_D = 3\text{ mA},$ $f = 900\text{ MHz}$
Minimum noise figure	Fmin	—	0.83	—	dB	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA},$ $f = 2\text{ GHz}$
Minimum noise figure	Fmin	—	1.08	—	dB	$V_{DS} = 3\text{ V}, I_D = 3\text{ mA},$ $f = 2\text{ GHz}$
Minimum noise figure	Fmin	—	0.52	1.0	dB	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA},$ $f = 900\text{ MHz}$
Minimum noise figure	Fmin	—	0.74	—	dB	$V_{DS} = 3\text{ V}, I_D = 3\text{ mA},$ $f = 900\text{ MHz}$

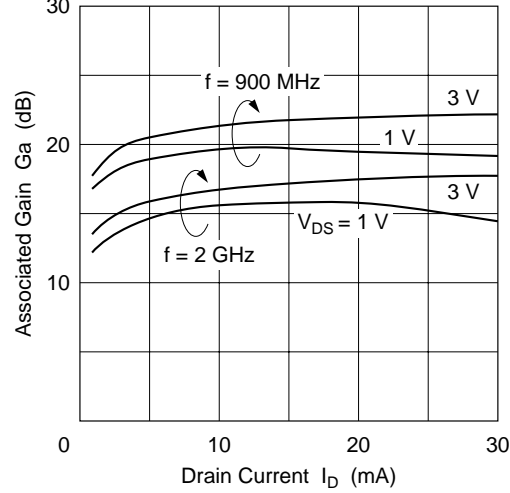
Note: Marking is “ZT—”.



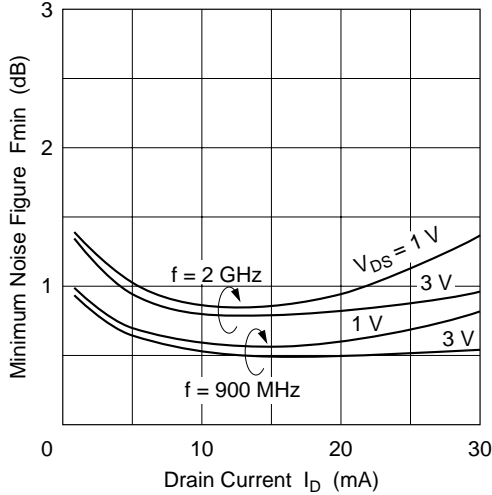
Forward Transfer Admittance vs. Drain Current



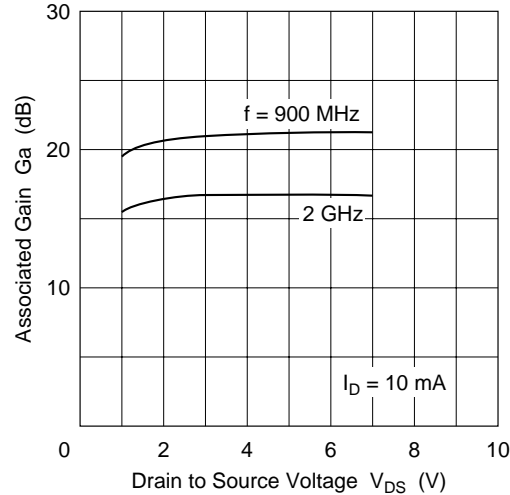
Associated Gain vs. Drain Current

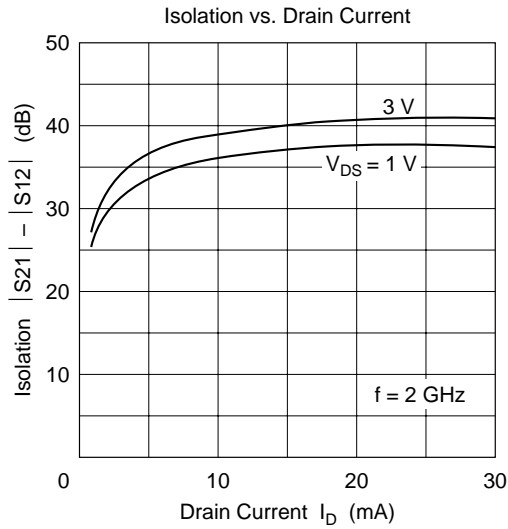
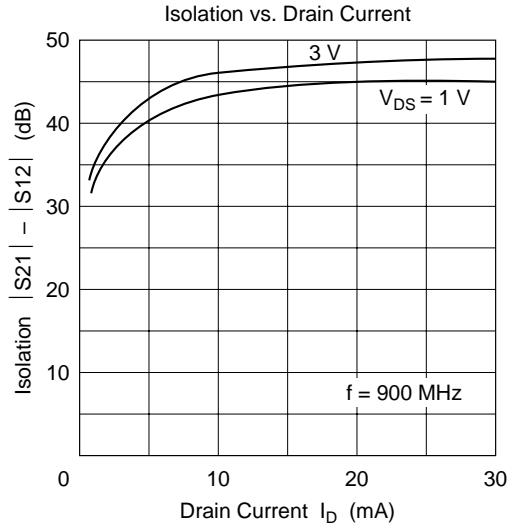
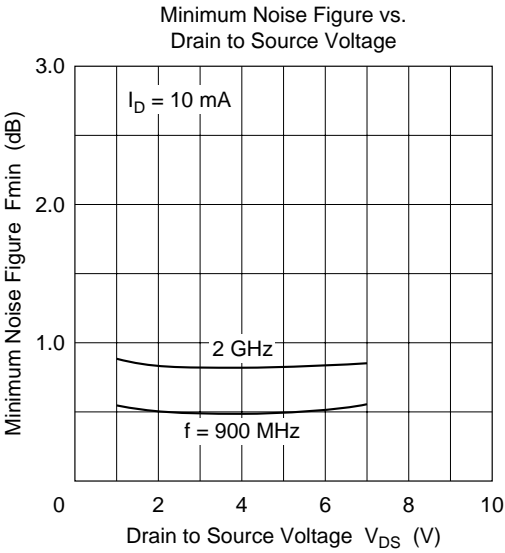


Minimum Noise Figure vs. Drain Current

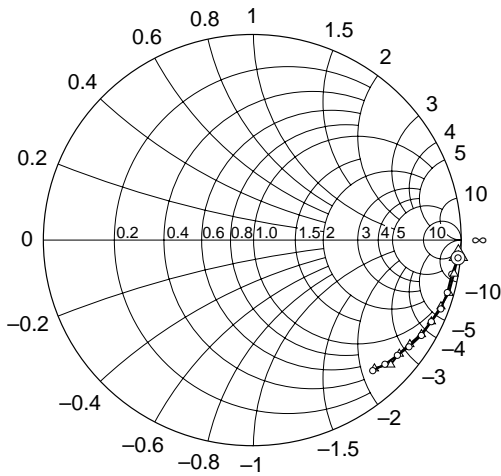


Associated Gain vs. Drain to Source Voltage



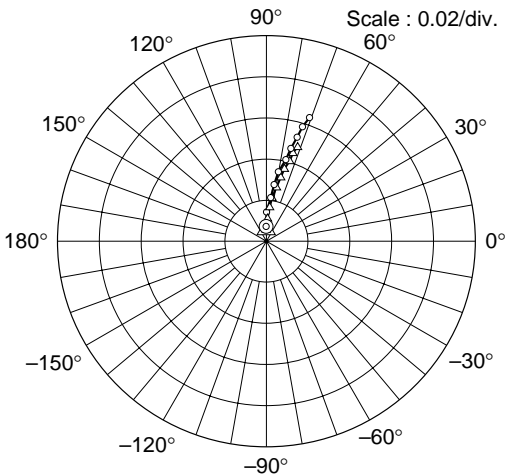


S11 Parameter vs. Frequency



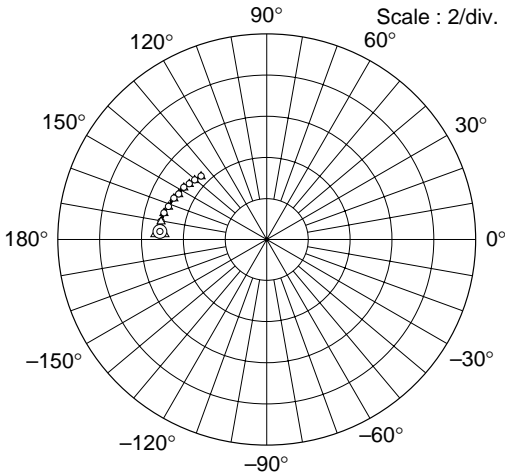
Condition : $I_D = 10\text{ mA}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)
○ ($V_{DS} = 1\text{ V}$)
△ ($V_{DS} = 3\text{ V}$)

S12 Parameter vs. Frequency



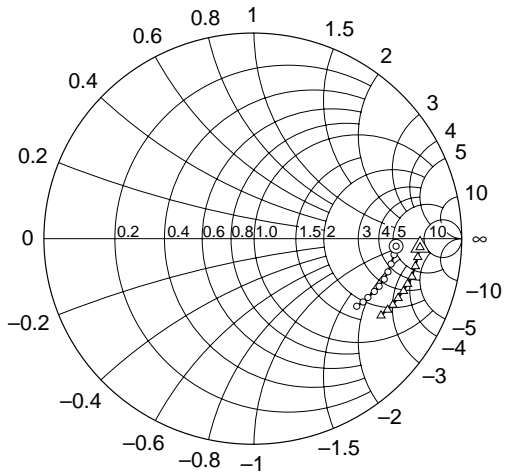
Condition : $I_D = 10\text{ mA}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)
○ ($V_{DS} = 1\text{ V}$)
△ ($V_{DS} = 3\text{ V}$)

S21 Parameter vs. Frequency



Condition : $I_D = 10\text{ mA}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)
○ ($V_{DS} = 1\text{ V}$)
△ ($V_{DS} = 3\text{ V}$)

S22 Parameter vs. Frequency



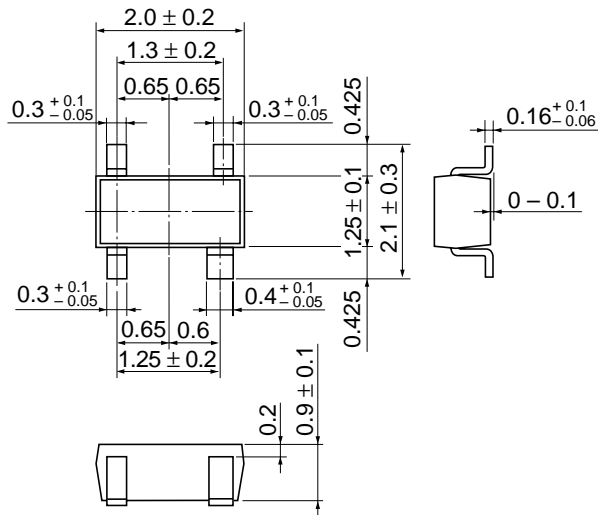
Condition : $I_D = 10\text{ mA}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)
○ ($V_{DS} = 1\text{ V}$)
△ ($V_{DS} = 3\text{ V}$)

S Parameter ($V_{DS} = 1\text{ V}$, $I_D = 10\text{ mA}$, $Z_O = 50\ \Omega$)

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.996	-4.8	5.12	175.8	0.00691	89.8	0.688	-3.2
400	0.980	-9.5	5.13	169.9	0.0143	88.2	0.682	-6.5
600	0.977	-15.0	5.07	165.4	0.0210	83.3	0.674	-10.6
800	0.970	-19.9	4.94	161.6	0.0276	81.5	0.668	-13.8
1000	0.952	-24.4	4.84	156.5	0.0399	79.3	0.658	-17.2
1200	0.938	-29.2	4.74	152.7	0.0404	76.0	0.648	-20.7
1400	0.916	-34.0	4.67	147.7	0.0462	74.8	0.636	-23.7
1600	0.896	-38.2	4.55	144.1	0.0523	73.1	0.622	-27.1
1800	0.882	-42.9	4.47	140.0	0.0578	72.0	0.611	-29.9
2000	0.859	-47.1	4.36	135.8	0.0630	70.3	0.597	-33.1

S Parameter ($V_{DS} = 3\text{ V}$, $I_D = 10\text{ mA}$, $Z_O = 50\ \Omega$)

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.998	-4.0	5.13	175.8	0.00581	89.8	0.802	-3.2
400	0.988	-9.2	5.14	170.1	0.0110	85.5	0.796	-6.5
600	0.978	-14.5	5.08	165.2	0.0163	83.3	0.790	-9.8
800	0.968	-19.4	4.95	161.4	0.0216	82.0	0.783	-13.3
1000	0.953	-24.2	4.85	156.4	0.0363	79.2	0.774	-16.4
1200	0.937	-28.7	4.75	152.5	0.0312	76.5	0.764	-19.4
1400	0.917	-33.3	4.68	147.8	0.0358	75.3	0.753	-22.5
1600	0.900	-37.5	4.57	144.0	0.0401	73.2	0.742	-25.4
1800	0.883	-41.9	4.49	140.1	0.0442	72.8	0.731	-28.1
2000	0.858	-46.1	4.37	135.9	0.0477	71.4	0.718	-31.1



Hitachi Code	CMPAK-4(T)
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.006 g

Datasheet Title

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
 Europe : <http://www.hitachi-eu.com/hel/ecg>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Domacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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